

74HC1GU04

Inverter

Rev. 05 — 10 July 2007

Product data sheet

1. General description

The 74HC1GU04 is a high-speed Si-gate CMOS device. It provides an inverting single stage function. The standard output currents are half those of the 74HCU04.

2. Features

- Symmetrical output impedance
- Wide operating voltage range from 2.0 V to 6.0 V
- Low power dissipation
- Balanced propagation delays
- SOT353-1 and SOT753 package options

3. Ordering information

Table 1. Ordering information

| Type number | Package | | | |
|-------------|-------------------|--------|------------------------------------------------------------------------|----------|
| | Temperature range | Name | Description | Version |
| 74HC1GU04GW | -40 °C to +125 °C | TSSOP5 | plastic thin shrink small outline package; 5 leads; body width 1.25 mm | SOT353-1 |
| 74HC1GU04GV | -40 °C to +125 °C | SC-74A | plastic surface-mounted package; 5 leads | SOT753 |

4. Marking

Table 2. Marking codes

| Type number | Marking |
|-------------|---------|
| 74HC1GU04GW | HD |
| 74HC1GU04GV | HU4 |

5. Functional diagram

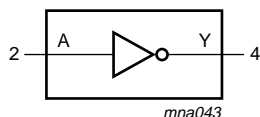


Fig 1. Logic symbol

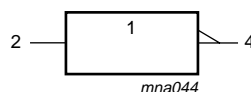


Fig 2. IEC logic symbol

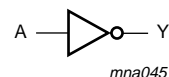


Fig 3. Logic diagram

6. Pinning information

6.1 Pinning

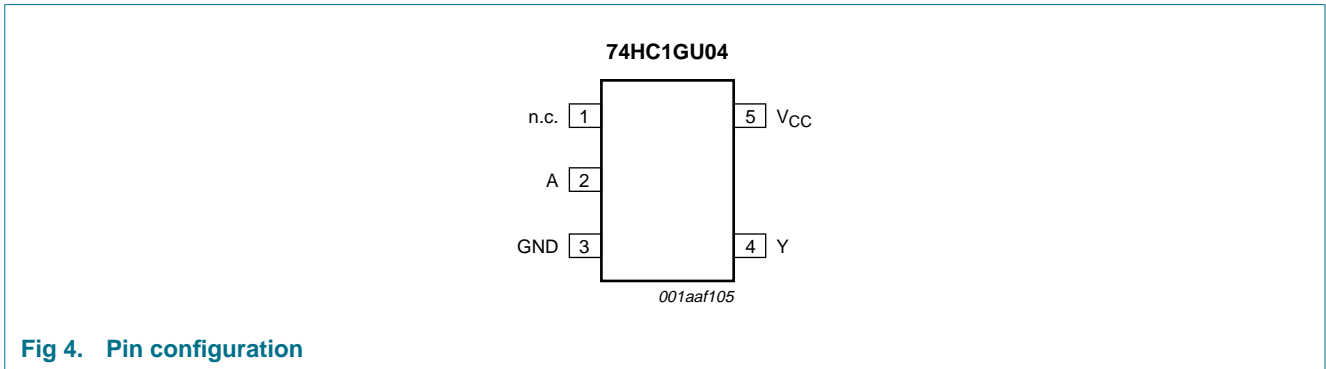


Fig 4. Pin configuration

6.2 Pin description

Table 3. Pin description

| Symbol | Pin | Description |
|-----------------|-----|----------------|
| n.c. | 1 | not connected |
| A | 2 | data input |
| GND | 3 | ground (0 V) |
| Y | 4 | data output |
| V _{CC} | 5 | supply voltage |

7. Functional description

Table 4. Function table

H = HIGH voltage level; L = LOW voltage level

| Input | Output |
|----------|----------|
| A | Y |
| L | H |
| H | L |

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

| Symbol | Parameter | Conditions | Min | Max | Unit |
|-----------|-------------------------|--------------------------------------------------------|-------|-------|------|
| V_{CC} | supply voltage | | -0.5 | +7.0 | V |
| I_{IK} | input clamping current | $V_I < -0.5\text{ V}$ or $V_I > V_{CC} + 0.5\text{ V}$ | [1] - | ±20 | mA |
| I_{OK} | output clamping current | $V_O < -0.5\text{ V}$ or $V_O > V_{CC} + 0.5\text{ V}$ | [1] - | ±20 | mA |
| I_O | output current | $-0.5\text{ V} < V_O < V_{CC} + 0.5\text{ V}$ | [1] - | ±12.5 | mA |
| I_{CC} | supply current | | - | 25 | mA |
| I_{GND} | ground current | | -25 | - | mA |
| T_{stg} | storage temperature | | -65 | +150 | °C |
| P_{tot} | total power dissipation | $T_{amb} = -40\text{ °C}$ to $+125\text{ °C}$ | [2] - | 200 | mW |

[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] Above 55 °C the value of P_{tot} derates linearity with 2.5 mW/K.

9. Recommended operating conditions

Table 6. Recommended operating conditions

Voltages are referenced to GND (ground = 0 V).

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|---------------------|-------------------------------------|-------------------------|-----|-----|----------|------|
| V_{CC} | supply voltage | | 2.0 | 5.0 | 6.0 | V |
| V_I | input voltage | | 0 | - | V_{CC} | V |
| V_O | output voltage | | 0 | - | V_{CC} | V |
| T_{amb} | ambient temperature | | -40 | +25 | +125 | °C |
| $\Delta t/\Delta V$ | input transition rise and fall rate | $V_{CC} = 2.0\text{ V}$ | - | - | 625 | ns/V |
| | | $V_{CC} = 4.5\text{ V}$ | - | - | 139 | ns/V |
| | | $V_{CC} = 6.0\text{ V}$ | - | - | 83 | ns/V |

10. Static characteristics

Table 7. Static characteristics

Voltages are referenced to GND (ground = 0 V). All typical values are measured at $T_{amb} = 25\text{ °C}$.

| Symbol | Parameter | Conditions | -40 °C to +85 °C | | | -40 °C to +125 °C | | Unit |
|----------|--------------------------|-------------------------|------------------|-----|-----|-------------------|-----|------|
| | | | Min | Typ | Max | Min | Max | |
| V_{IH} | HIGH-level input voltage | $V_{CC} = 2.0\text{ V}$ | 1.7 | 1.4 | - | 1.7 | - | V |
| | | $V_{CC} = 4.5\text{ V}$ | 3.6 | 2.6 | - | 3.6 | - | V |
| | | $V_{CC} = 6.0\text{ V}$ | 4.8 | 3.4 | - | 4.8 | - | V |
| V_{IL} | LOW-level input voltage | $V_{CC} = 2.0\text{ V}$ | - | 0.6 | 0.3 | - | 0.3 | V |
| | | $V_{CC} = 4.5\text{ V}$ | - | 1.9 | 0.9 | - | 0.9 | V |
| | | $V_{CC} = 6.0\text{ V}$ | - | 2.6 | 1.2 | - | 1.2 | V |

Table 7. Static characteristics ...continued

Voltages are referenced to GND (ground = 0 V). All typical values are measured at $T_{amb} = 25\text{ }^{\circ}\text{C}$.

| Symbol | Parameter | Conditions | -40 °C to +85 °C | | | -40 °C to +125 °C | | Unit |
|-----------------|---------------------------|----------------------------------------------------------------------------------------|------------------|------|------|-------------------|-----|------|
| | | | Min | Typ | Max | Min | Max | |
| V _{OH} | HIGH-level output voltage | V _I = V _{IH} or V _{IL} | | | | | | |
| | | I _O = -20 μA; V _{CC} = 2.0 V | 1.8 | 2.0 | - | 1.8 | - | V |
| | | I _O = -20 μA; V _{CC} = 4.5 V | 4.0 | 4.5 | - | 4.0 | - | V |
| | | I _O = -20 μA; V _{CC} = 6.0 V | 5.5 | 6.0 | - | 5.5 | - | V |
| | | I _O = -2.0 mA; V _{CC} = 4.5 V | 4.13 | 4.32 | - | 3.7 | - | V |
| | | I _O = -2.6 mA; V _{CC} = 6.0 V | 5.63 | 5.81 | - | 5.2 | - | V |
| V _{OL} | LOW-level output voltage | V _I = V _{IH} or V _{IL} | | | | | | |
| | | I _O = 20 μA; V _{CC} = 2.0 V | - | 0 | 0.2 | - | 0.2 | V |
| | | I _O = 20 μA; V _{CC} = 4.5 V | - | 0 | 0.5 | - | 0.5 | V |
| | | I _O = 20 μA; V _{CC} = 6.0 V | - | 0 | 0.5 | - | 0.5 | V |
| | | I _O = 2.0 mA; V _{CC} = 4.5 V | - | 0.15 | 0.33 | - | 0.4 | V |
| | | I _O = 2.6 mA; V _{CC} = 6.0 V | - | 0.16 | 0.33 | - | 0.4 | V |
| I _I | input leakage current | V _I = V _{CC} or GND; V _{CC} = 6.0 V | - | - | 1.0 | - | 1.0 | μA |
| I _{CC} | supply current | V _I = V _{CC} or GND; I _O = 0 A; V _{CC} = 6.0 V | - | - | 10 | - | 20 | μA |
| C _I | input capacitance | | - | 5 | - | - | - | pF |

11. Dynamic characteristics

Table 8. Dynamic characteristics

GND = 0 V; $t_r = t_f = 6.0\text{ ns}$; For test circuit see [Figure 6](#). All typical values are measured at $T_{amb} = 25\text{ }^{\circ}\text{C}$.

| Symbol | Parameter | Conditions | -40 °C to +85 °C | | | -40 °C to +125 °C | | Unit |
|-----------------|-------------------------------|-------------------------------------------------------------|------------------|-----|-----|-------------------|-----|------|
| | | | Min | Typ | Max | Min | Max | |
| t _{pd} | propagation delay | A to Y; see Figure 5 [1] | | | | | | |
| | | V _{CC} = 2.0 V; C _L = 50 pF | - | 10 | 90 | - | 105 | ns |
| | | V _{CC} = 4.5 V; C _L = 50 pF | - | 7 | 18 | - | 21 | ns |
| | | V _{CC} = 6.0 V; C _L = 50 pF | - | 6 | 15 | - | 18 | ns |
| | | V _{CC} = 5.0 V; C _L = 15 pF | - | 5 | - | - | - | ns |
| C _{PD} | power dissipation capacitance | V _I = GND to V _{CC} [2] | - | 14 | - | - | - | pF |

[1] t_{pd} is the same as t_{PLH} and t_{PHL}.

[2] C_{PD} is used to determine the dynamic power dissipation P_D (μW).

$$P_D = C_{PD} \times V_{CC}^2 \times f_i + \sum (C_L \times V_{CC}^2 \times f_o) \text{ where:}$$

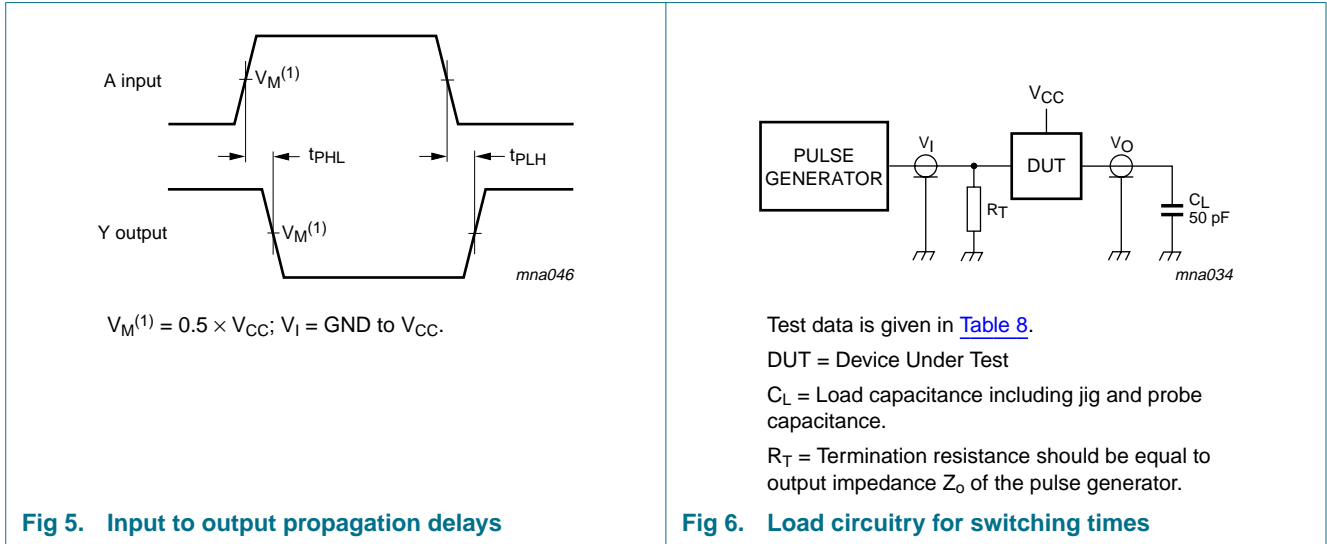
f_i = input frequency in MHz;

f_o = output frequency in MHz;

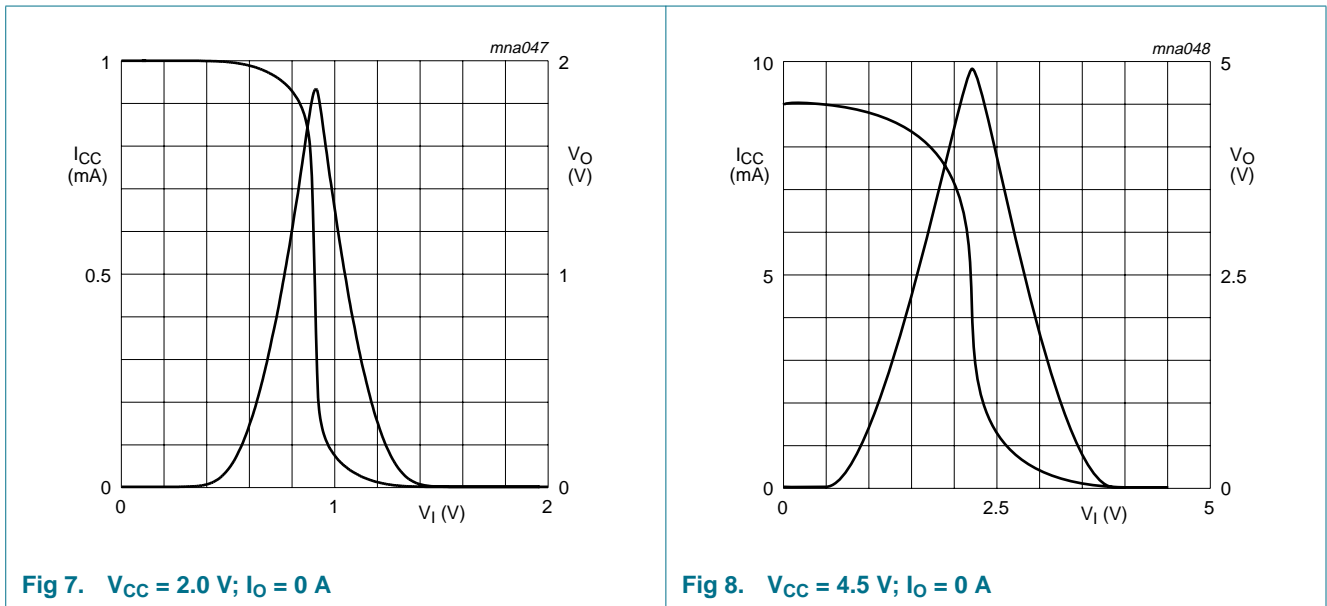
C_L = output load capacitance in pF;

V_{CC} = supply voltage in Volts.

12. Waveforms



13. Typical transfer characteristics



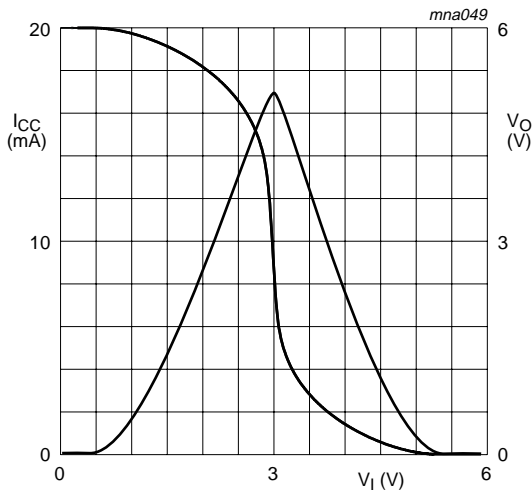


Fig 9. $V_{CC} = 6.0\text{ V}$; $I_o = 0\text{ A}$

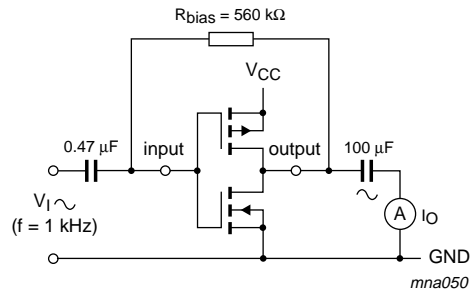


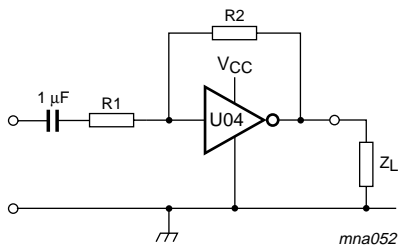
Fig 10. Test set-up for measuring forward transfer conductance $g_{fs} = \Delta I_o / \Delta V_i$ at V_o is constant

14. Application information

Some applications are:

- Linear amplifier (see [Figure 11](#))
- In crystal oscillator design (see [Figure 12](#))

Remark: All values given are typical unless otherwise specified



Maximum $V_{o(p-p)} = V_{CC} - 1.5\text{ V}$ centered at $0.5 \times V_{CC}$.

$$G_v = -\frac{G_{ol}}{1 + \frac{R1}{R2}(1 + G_{ol})}$$

G_{ol} = open loop gain

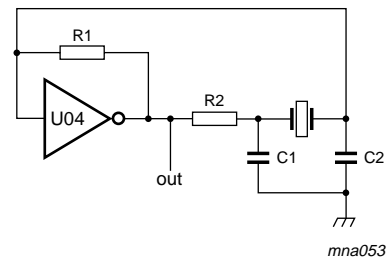
G_v = voltage gain

$R1 \geq 3\text{ k}\Omega$, $R2 \leq 1\text{ M}\Omega$

$Z_L > 10\text{ k}\Omega$; $G_{ol} = 20$ (typ.)

Typical unity gain bandwidth product is 5 MHz.

Fig 11. Used as a linear amplifier



$C1 = 47\text{ pF}$ (typ.)

$C2 = 22\text{ pF}$ (typ.)

$R1 = 1\text{ M}\Omega$ to $10\text{ M}\Omega$ (typ.)

$R2$ optimum value depends on the frequency and required stability against changes in V_{CC} or average minimum I_{CC} (I_{CC} is typically 2 mA at $V_{CC} = 3\text{ V}$ and $f = 1\text{ MHz}$).

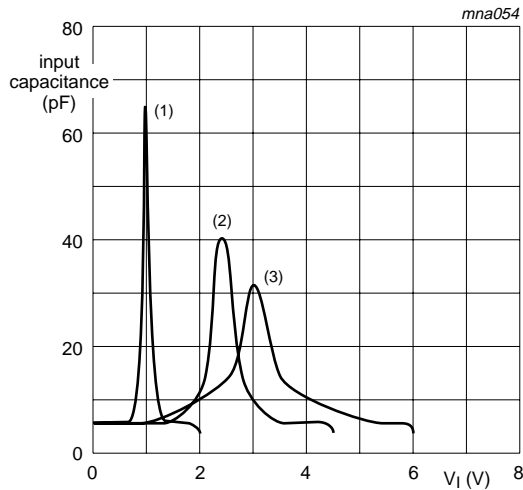
Fig 12. Crystal oscillator configuration

Table 9. External components for resonator (f < 1 MHz)
 All values given are typical and must be used as an initial set-up

| Frequency | R1 | R2 | C1 | C2 |
|----------------------|--------|--------|-------|-------|
| 10 kHz to 15.9 kHz | 2.2 MΩ | 220 kΩ | 56 pF | 20 pF |
| 16 kHz to 24.9 kHz | 2.2 MΩ | 220 kΩ | 56 pF | 10 pF |
| 25 kHz to 54.9 kHz | 2.2 MΩ | 100 kΩ | 56 pF | 10 pF |
| 55 kHz to 129.9 kHz | 2.2 MΩ | 100 kΩ | 47 pF | 5 pF |
| 130 kHz to 199.9 kHz | 2.2 MΩ | 47 kΩ | 47 pF | 5 pF |
| 200 kHz to 349.9 kHz | 2.2 MΩ | 47 kΩ | 47 pF | 5 pF |
| 350 kHz to 600 kHz | 2.2 MΩ | 47 kΩ | 47 pF | 5 pF |

Table 10. Optimum value for R2

| Frequency | R2 | Optimum for |
|-----------|--------|----------------------------------------------------|
| 3 kHz | 2.0 kΩ | minimum required I _{CC} |
| | 8.0 kΩ | minimum influence due to change in V _{CC} |
| 6 kHz | 1.0 kΩ | minimum required I _{CC} |
| | 4.7 kΩ | minimum influence by V _{CC} |
| 10 kHz | 0.5 kΩ | minimum required I _{CC} |
| | 2.0 kΩ | minimum influence by V _{CC} |
| 14 kHz | 0.5 kΩ | minimum required I _{CC} |
| | 1.0 kΩ | minimum influence by V _{CC} |
| >14 kHz | - | replace R2 by C3 with a typical value of 35 pF |



- (1) V_{CC} = 2.0 V.
- (2) V_{CC} = 4.5 V.
- (3) V_{CC} = 6.0 V.

Fig 13. Typical input capacitance as a function of the input voltage

15. Package outline

TSSOP5: plastic thin shrink small outline package; 5 leads; body width 1.25 mm

SOT353-1

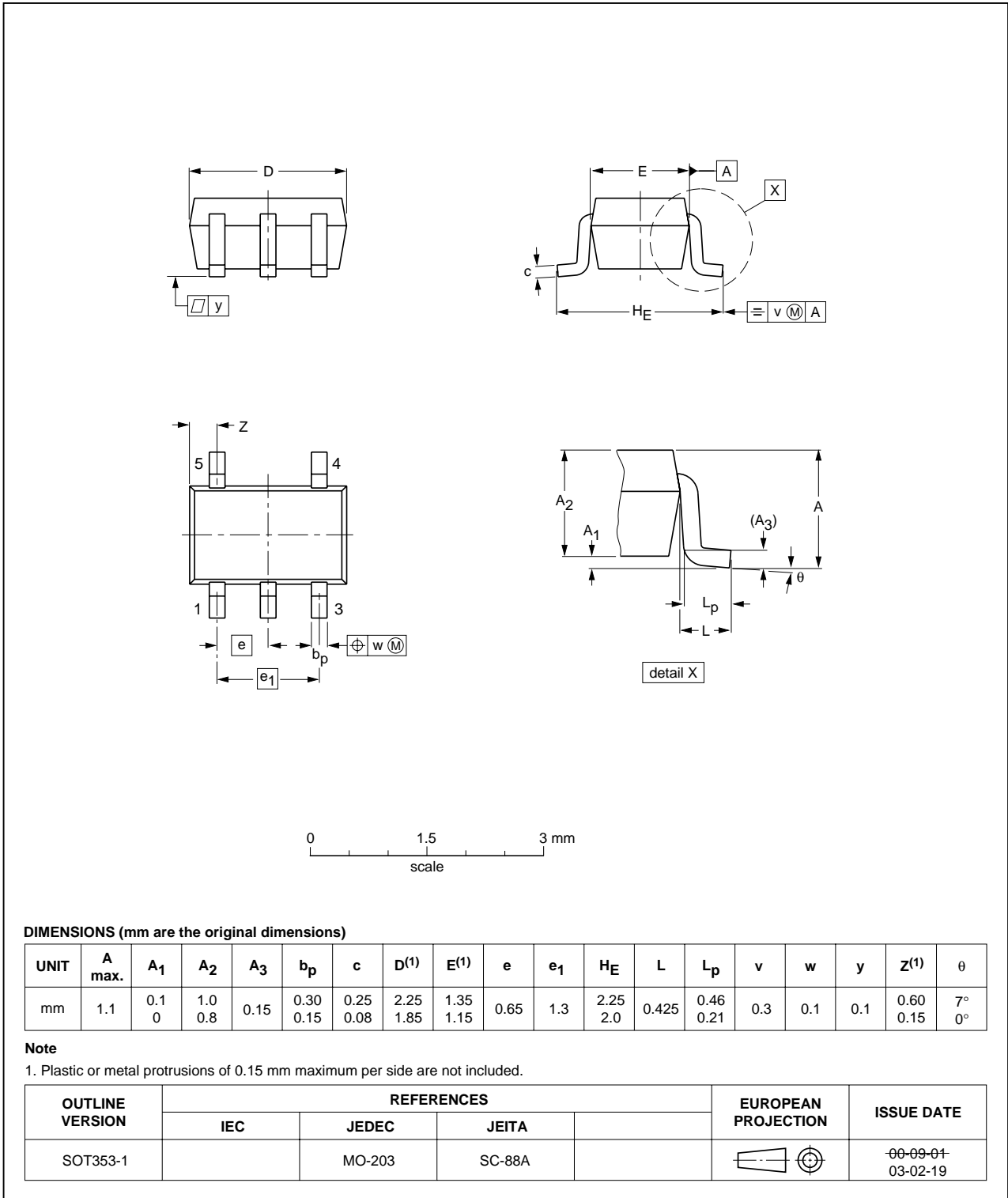


Fig 14. Package outline SOT353-1 (TSSOP5)

Plastic surface-mounted package; 5 leads

SOT753

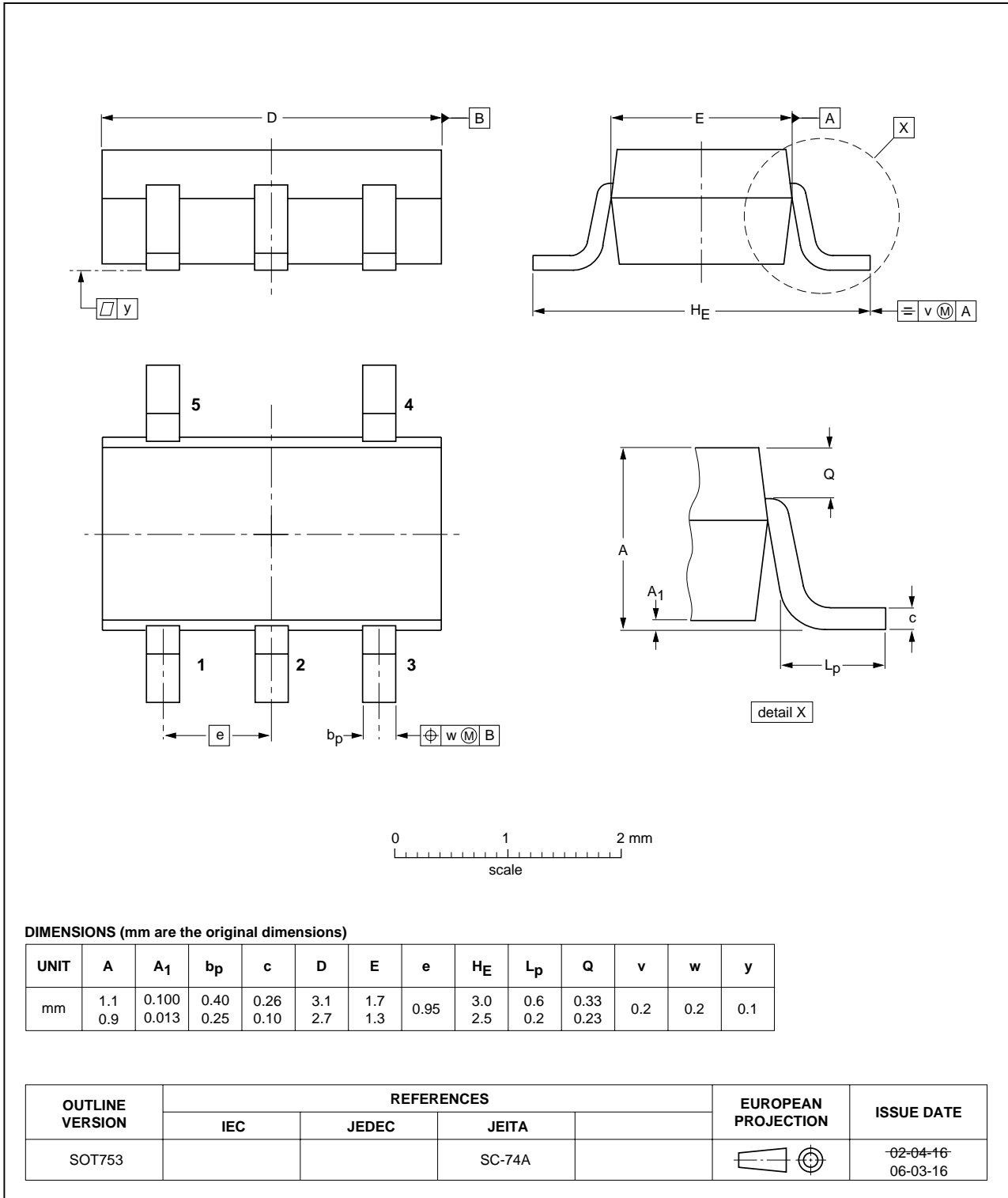


Fig 15. Package outline SOT753 (SC-74A)

16. Revision history

Table 11. Revision history

| Document ID | Release date | Data sheet status | Change notice | Supersedes |
|----------------|--------------|----------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|---------------|-------------|
| 74HC1GU04_5 | 20070710 | Product data sheet | - | 74HC1GU04_4 |
| Modifications: | | <ul style="list-style-type: none">• The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors.• Legal texts have been adapted to the new company name where appropriate.• Package SOT353 changed to SOT353-1 in Table 1 and Figure 14.• Quick Reference Data and Soldering sections removed.• Section 2 "Features" updated. | | |
| 74HC1GU04_4 | 20020527 | Product specification | - | 74HC1GU04_3 |
| 74HC1GU04_3 | 20020513 | Product specification | - | 74HC1GU04_2 |
| 74HC1GU04_2 | 20010427 | Product specification | - | 74HC1GU04_1 |
| 74HC1GU04_1 | 19981118 | Product specification | - | - |

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| Document status ^{[1][2]} | Product status ^[3] | Definition |
|-----------------------------------|-------------------------------|---------------------------------------------------------------------------------------|
| Objective [short] data sheet | Development | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification | This document contains data from the preliminary specification. |
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[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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